

N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)		
150	0.247 at V _{GS} = 10 V	15		
	0.255 at V _{GS} = 4.5 V	13		

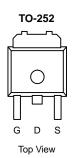
FEATURES

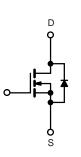
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g Tested



APPLICATIONS

• Primary Side Switch





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C =	= 25 °C, unless othe	rwise noted)			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	150	V	
Gate-Source Voltage		V _{GS}	± 20	- V	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C		15		
	T _C = 125 °C		8.7		
Pulsed Drain Current		I _{DM}	45	A	
Continuous Source Current (Diode Conduction)		۱ _S	15		
Avalanche Current		I _{AR}	12		
Repetitive Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AR}	11.3	mJ	
Maximum Dawar Dissinction	T _C = 25 °C	P _D	62 ^b	W	
Maximum Power Dissipation	T _A = 25 °C	טי	2.7 ^a	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
lungting to Ambiguid	t ≤ 10 s	R _{thJA}	16	20	°C/W
Junction-to-Ambient ^a	Steady State		45	55	
Junction-to-Case		R _{thJC}	2	2.4	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. See SOA curve for voltage derating.

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Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static				.,,,,,			
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	150			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	2				
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = 150 V, V _{GS} = 0 V			1		
	I _{DSS}	V _{DS} = 150 V, V _{GS} = 0 V, T _J = 125 °C			50	μA	
		V _{DS} = 150 V, V _{GS} = 0 V, T _J = 175 °C			250		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	15			А	
Drain-Source On-State Resistance ^b		V _{GS} = 10 V, I _D = 10 A		0.247			
	Р	V _{GS} = 10 V, I _D = 10 A, T _J = 125 °C		0.258		Ω	
	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A, T _J = 175 °C		0.279			
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		0.255			
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		25		S	
Dynamic ^a		·					
Input Capacitance	C _{iss}			900		pF	
Output Capacitance	C _{oss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		115			
Reverse Transfer Capacitance	C _{rss}			70			
Total Gate Charge ^c	Qg			20	25		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$		5.5		nC	
Gate-Drain Charge ^c	Q _{gd}			7			
Gate Resistance	Rg		1		3.2	Ω	
Turn-On Delay Time ^c	t _{d(on)}			8	12		
Rise Time ^c	t _r	$V_{DD} = 75 \text{ V}, \text{ R}_{L} = 5 \Omega$ $I_{D} \cong 10 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_{G} = 2.5$		35	55	ns	
Turn-Off Delay Time ^c	t _{d(off)}			17	25		
Fall Time ^c	t _f	Ω		30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	_C = 25 °C)					
Pulsed Current	I _{SM}				45	А	
Diode Forward Voltage ^b	V_{SD}	I _F = 10 A, V _{GS} = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 10 A, dI/dt = 100 A/µs		55	85	ns	

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

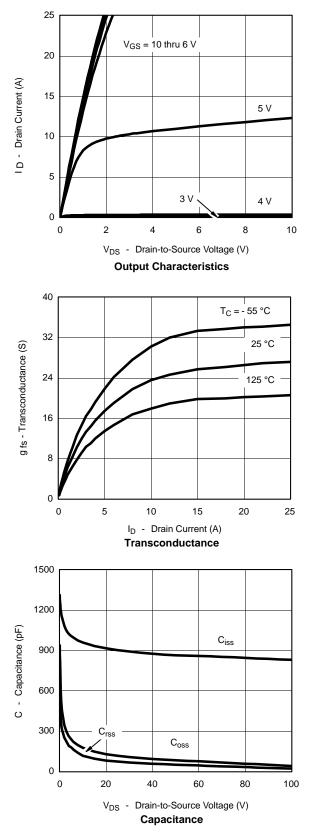
c. Independent of operating temperature.

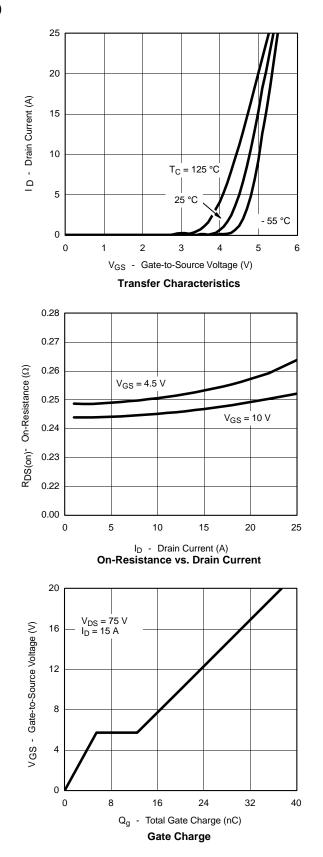
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS (25 °C unless noted)



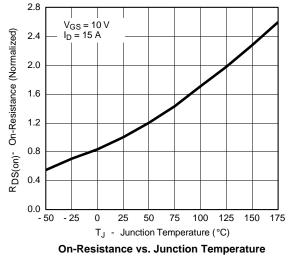


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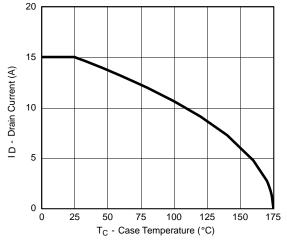
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10

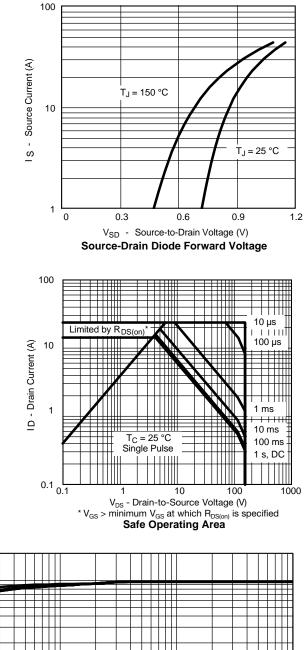
TYPICAL CHARACTERISTICS (25 °C unless noted)



THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



0.02 0.05 1 Single Pulse



2

1

0.1

0.01

10-4

Normalized Effective Transient Thermal Impedance Duty Cycle = 0.5

0.2 0.1

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